

[PHOTO SENSOR AND METHOD OF FORMING THE SAME]

Abstract of Disclosure

A method of forming a photo sensor in a photo diode is provided. The photo diode is formed in a semiconductor wafer. The semiconductor wafer includes a substrate with a first conductive type, and an insulating layer surrounding the photo sensor. A first ion implantation process, utilizing dopants with a second conductive type, is performed to form a plurality of first doped regions in the surface of the photo sensor. A second ion implantation process, utilizing dopants with the second conductive type, is performed to form a second doped region in the surface of the photo sensor. The second doped region is overlapped with a portion of each of the first doped regions.

Figures